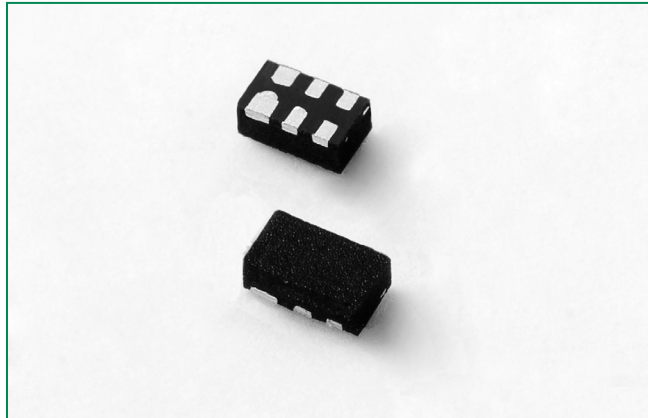


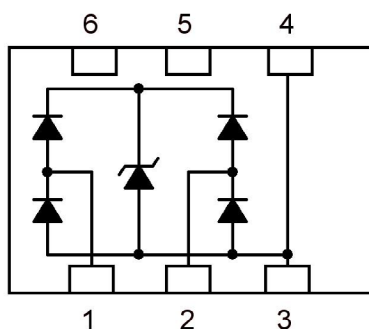
SP3014 Series 1.0pF, 15kV Diode Array



Pinout

I/O1	1	6	NC
I/O2	2	5	NC
GND	3	4	GND

Functional Block Diagram



Additional Information



Datasheet



Resources



Samples

Life Support Note:

Not Intended for Use in Life Support or Life Saving Applications

The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.

Description

The SP3014 series integrates 2 channels of low capacitance steering diodes and an additional zener diode to provide protection for electronic equipment that may experience destructive electrostatic discharges (ESD). The SP3014 can safely absorb repetitive ESD strikes above the maximum level specified in the IEC61000-4-2 international standard ($\pm 8\text{kV}$ contact discharge) without performance degradation.

The low loading capacitance makes it ideal for protecting high-speed signal lines such as USB2.0 and 1Gb Ethernet with an extremely low dynamic resistance to protect the most sensitive, state of the art chipsets against ESD transients.

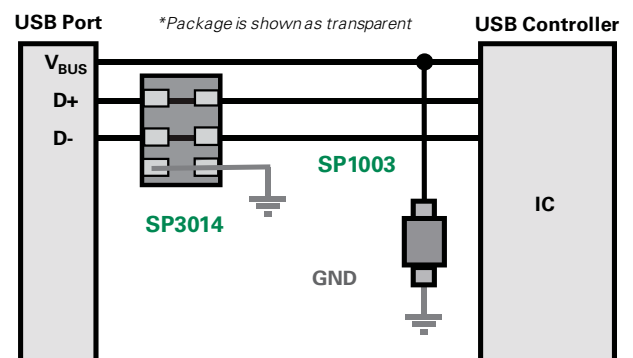
Features

- ESD, IEC61000-4-2, $\pm 15\text{kV}$ contact, $\pm 25\text{kV}$ air
- EFT, IEC61000-4-4, 80A ($t_p=5/50\text{ns}$)
- Lightning, IEC61000-4-5, 8A ($t_p=8/20\mu\text{s}$)
- Low capacitance of 1.0pF (TYP) per I/O
- Low leakage current of 1.0 μA (MAX) at 5V
- Small form factor μDFN (JEDEC MO-229) package provides flow through routing to simplify PCB layout
- AEC-Q101 qualified

Applications

- LCD/PDP TVs
- External Storages
- DVD/Blu-ray Players
- Set Top Boxes
- Smartphones
- Ultrabooks/Notebooks
- Digital Cameras
- Portable Medical
- Automotive Electronics
- Wearable Technology

USB 2.0 Protection Application Example



Absolute Maximum Ratings

Symbol	Parameter	Value	Units
I_{PP}	Peak Current ($t_p=8/20\mu s$)	8.0	A
T_{OP}	Operating Temperature	-40 to 125	°C
T_{STOR}	Storage Temperature	-55 to 150	°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

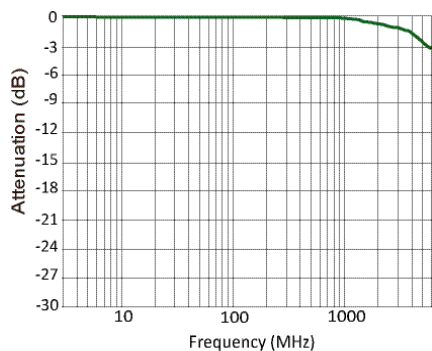
Electrical Characteristics ($T_{OP}=25^\circ C$)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V_{RWM}	$I_R \leq 1\mu A$			5.0	V
Reverse Leakage Current	I_{LEAK}	$V_R=5V$, Any I/O to GND			1.0	μA
Clamp Voltage ¹	V_C	$I_{PP}=1A$, $t_p=8/20\mu s$, Fwd		6.6		V
		$I_{PP}=2A$, $t_p=8/20\mu s$, Fwd		6.8		V
Dynamic Resistance ¹	R_{DYN}	$(V_{C2} - V_{C1}) / (I_{PP2} - I_{PP1})$		0.2		Ω
Dynamic Resistance ²	R_{DYN}	TLP, $t_p=100ns$, I/O to GND		0.25		Ω
ESD Withstand Voltage ¹	V_{ESD}	IEC61000-4-2 (Contact)	± 15			kV
		IEC61000-4-2 (Air)	± 25			kV
Diode Capacitance ¹	$C_{I/O-GND}$	Reverse Bias=0V, $f=1$ MHz		1.0		pF
Diode Capacitance ¹	$C_{I/O-I/O}$	Reverse Bias=0V, $f=1$ MHz		0.5		pF

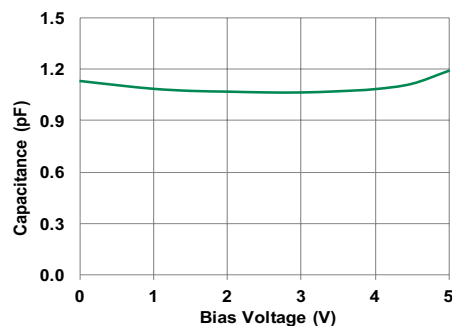
Note: 1 Parameter is guaranteed by design and/or device characterization.

2. Transmission Line Pulse (TLP) with 100ns width and 200ps rise time.

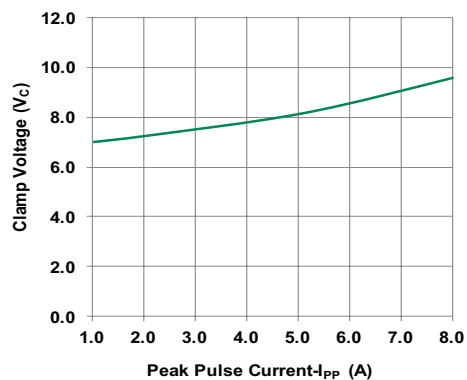
Insertion Loss (S21) I/O to GND



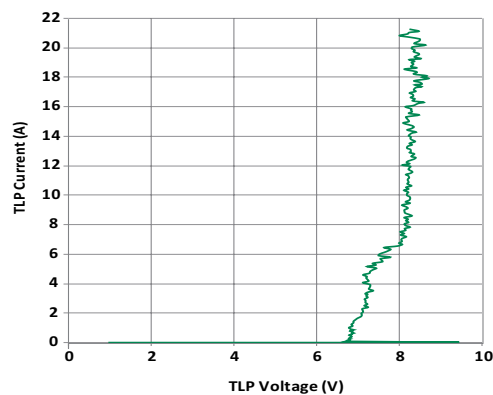
Capacitance vs. Reverse Bias



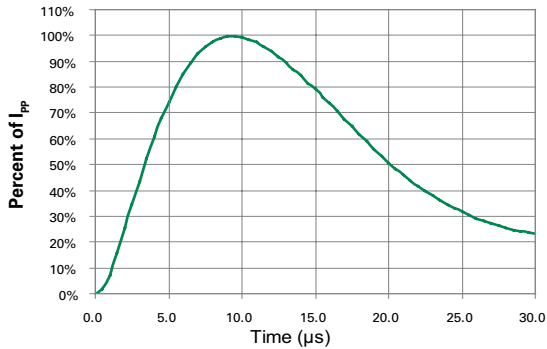
Clamping Voltage vs. I_{PP}



Transmission Line Pulse (TLP)

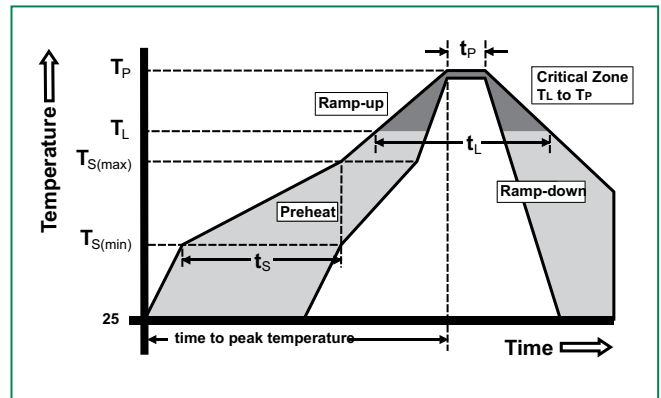


Pulse Waveform



Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus) Temp (T_L) to peak		3°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_P)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		6°C/second max
Time 25°C to peak Temperature (T_P)		8 minutes Max.
Do not exceed		260°C



Ordering Information

Part Number	Package	Marking	Min. Order Qty.
SP3014-02UTG	μDFN-6L	Ⓟ H2	3000

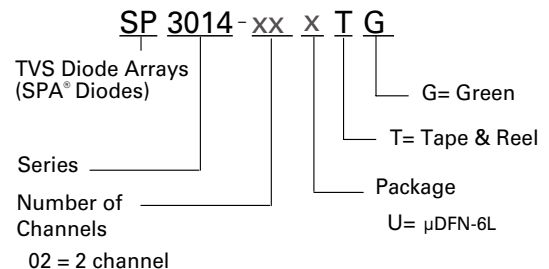
Product Characteristics

Lead Plating	Pre-Plated Frame (μDFN)
Lead Material	Copper Alloy
Lead Coplanarity	0.0004 inches (0.102mm)
Substrate material	Silicon
Body Material	Molded Epoxy
Flammability	UL 94 V-0

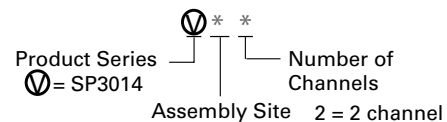
Notes :

1. All dimensions are in millimeters
2. Dimensions include solder plating.
3. Dimensions are exclusive of mold flash & metal burr.
4. Blo is facing up for mold and facing down for trim/form, i.e. reverse trim/form.
5. Package surface matte finish VDI 11-13.

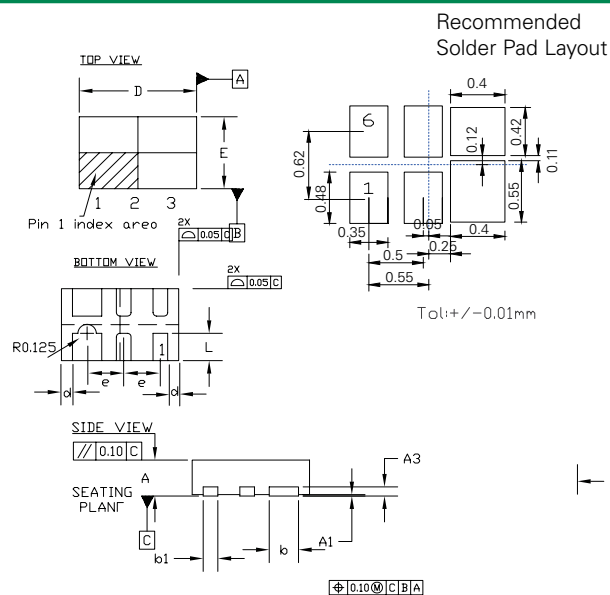
Part Numbering System



Part Marking System



Package Dimensions —μDFN-6L



Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9